

ABSTRACT OF THE DISCLOSURE

There is provided a magnetic memory including first and second wirings intersecting each other and disposed apart from each other, a magnetoresistance effect film positioned between the first and second wirings, and a first magnetic film including a first portion facing the magnetoresistance effect film with the first wiring interposed therebetween and a pair of second portions positioned on both sides of the first wiring and magnetically connected to the first portion, each of the first and second portions having either one of a high saturation magnetization soft magnetic material containing cobalt and a metal-nonmetal nano-granular film.